

SLD343YT

4W High Power Laser Diode

Preliminary

Description

The SLD343YT has a compatible package, and allows independent thermal and electric design.

It is a high power laser diode that affords easy optical design.

Features

- High-optical power output
 Recommended optical power output: Po = 4.0W
- High-optical power density: 4W/200µm

(Emitting line width)

Applications

- Solid state laser excitation
- Medical use
- Material processing
- Measurement

Structure

AlGaAs quantum well structure laser diode

Operating Lifetime

MTTF 10,000H (effective value) at Po = 4.0W, Tth = 25°C

Absolute Maximum Ratings (Tth = 25°C)

Optical power output
 Reverse voltage
 VR
 LD
 2
 V
 PD
 15
 V

Operating temperature (Tth) Topr −10 to +30 °C

• Storage temperature Tstg -40 to +85 °C

Warranty

This warranty period shall be 90 days after receipt of the product or 1,000 hours operation time whichever is shorter.

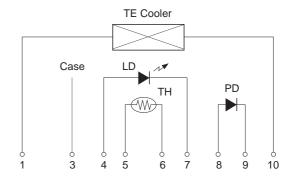
Sony Quality Assurance Department shall analyze any product that fails during said warranty period, and if the analysis results show that the product failed due to material or manufacturing defects on the part of Sony, the product shall be replaced free of charge.

Laser diodes naturally have differing lifetimes which follow a Weibull distribution.

Special warranties are also available.

M-288

Equivalent Circuit



Pin Configuration (Top View)

No.	Function
1	TE cooler (negative)
2	_
3	Case
4	Laser diode (anode)
5	Thermistor
6	Thermistor
7	Laser diode (cathode)
8	Photo diode (anode)
9	Photo diode (cathode)
10	TE cooler (positive)

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Electrical and Optical Characteristics

(Tth = Thermistor temperature, Tth = 25°C)

Item		Symbol	Conditions	Min.	Тур.	Max.	Unit
Threshold current		Ith			1.0	2.0	А
Operating current		lop	Po = 4.0W		4.6	6.5	А
Operating voltage		Vop	Po = 4.0W		2.0	3.0	V
Wavelength*		λρ	Po = 4.0W	790		840	nm
Radiation angle	Perpendicular	θΤ	Po = 4.0W	10	23	35	degree
	Parallel	θ//		5	10	15	degree
Positional accuracy	Position	ΔΧ, ΔΥ	Po = 4.0W			±100	μm
	Angle	Δφ⊥				±3	degree
		Δφ//				±4	degree
Differential efficiency		ηο	Po = 4.0W	0.5	1.1	1.5	W/A
Monitor current		Imon	Po = 4.0W Vr = 10V	0.2	1.0	4.0	mA
Thermistor resistance		Rth	Tth = 25°C		10		kΩ

* Wavelength Selection Classification

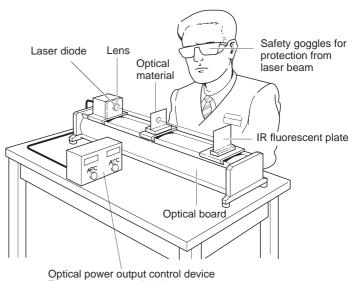
Туре	Wavelength (nm)
SLD343YT-1	795 ± 5
SLD343YT-2	810 ± 10
SLD343YT-3	830 ± 10

Туре	Wavelength (nm)
SLD343YT-21	798 ± 3
SLD343YT-24	807 ± 3
SLD343YT-25	810 ± 3

Handling Precautions

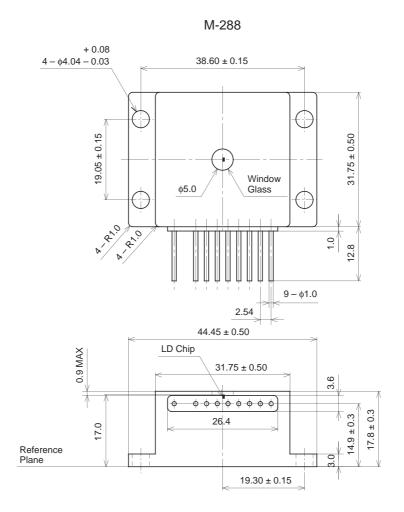
Eye protection against laser beams

The optical output of laser diodes ranges from several mW to 10W. However the optical power density of the laser beam at the diode chip reaches 1.5MW/cm2. Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.



Temperature control device

Package Outline Unit: mm



SONY CODE	M-288
EIAJ CODE	
JEDEC CODE	

PACKAGE WEIGHT	150g
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